Fast recovery diode

RF073M2S

●Applications

High frequency rectification

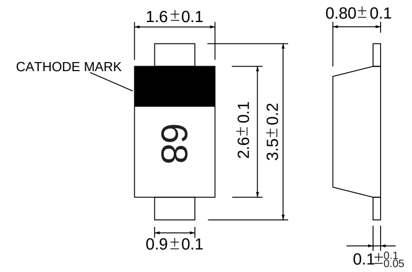
●Features

1) Small power mold type (PMDS)
2) Ultra low V_F
3) Very fast recovery
4) Low switching loss

●Construction

Silicon epitaxial planar

●External dimensions (Unit : mm)



ROHM : PMDU

●Absolute maximum ratings (Ta=25°C)

Parameter	Symbol	Limits	Unit
Reverse voltage (repetitive peak)	V_{RM}	200	V
Reverse voltage (DC)	V_R	200	V
Forward voltage (DC)	I_F *	1.0	A
Average rectified forward current	I_O *	0.7	A
Forward peak surge current (60Hz · 1cyc.)	I_{FSM}	15	A
Junction temperature	Tj	150	°C
Storage temperature	Tstg	−55 to +150	°C

* Tc max=120°C Mounting on glass epoxi board

●Electrical characteristics (Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F	–	0.830	0.890	V	I_F=0.7A
Reverse current	I_R	–	1.2	10	µA	V_R=200V
Reverse recovery time	t_{rr}	–	9	20	ns	I_F=0.5A, I_R=1.0A, I_{rr}=0.25×I_R

Note) ESD sensitive product handing required.

●**Electrical characteristic curves** (Ta=25°C)

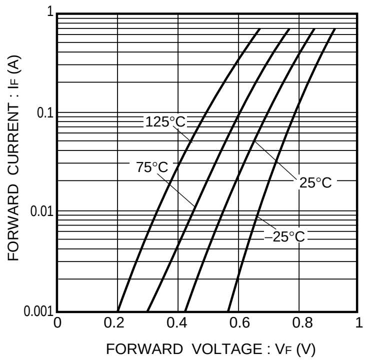


Fig.1 Forward temperature characteristics

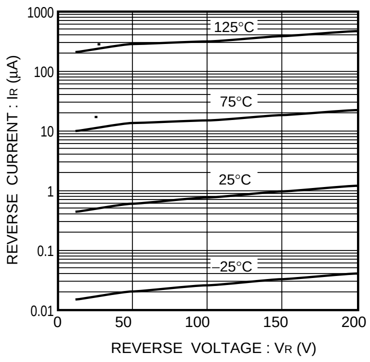


Fig.2 Reverse temperature characteristics

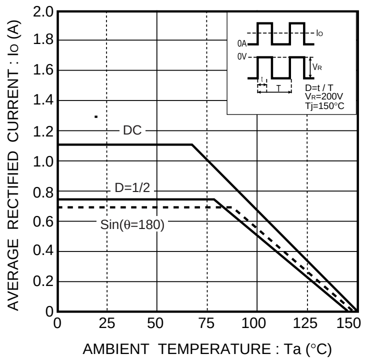


Fig.3 Derating curve

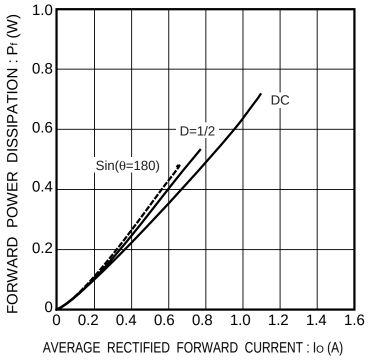


Fig. 4 Power dissipation characteristics

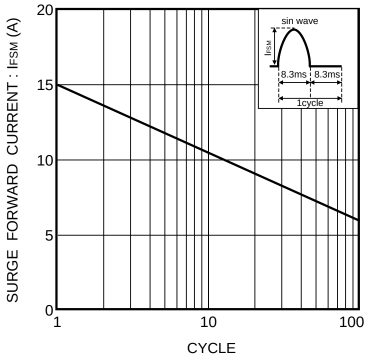


Fig.5 Forward peak surge current

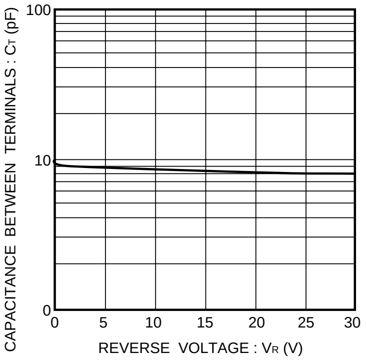


Fig. 6 Capacitance between terminals characteristics